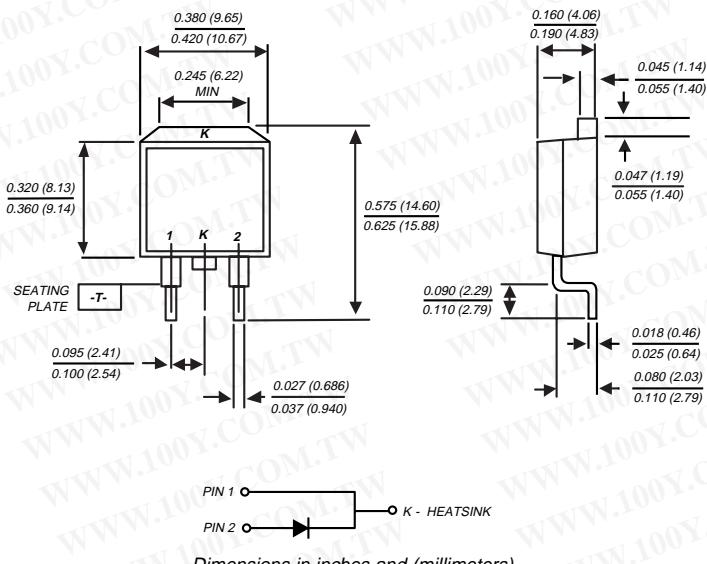


MBRB735 THRU MBRB760

SCHOTTKY RECTIFIER

Reverse Voltage - 35 to 60 Volts Forward Current - 7.5 Amperes

TO-263AB



Dimensions in inches and (millimeters)

FEATURES

- ◆ Plastic package has Underwriters Laboratory Flammability Classifications 94V-0
- ◆ Metal silicon junction majority carrier conduction
- ◆ Low power loss, high efficiency
- ◆ High current capability, low forward voltage drop
- ◆ High surge capability
- ◆ For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications
- ◆ Guardring for overvoltage protection
- ◆ High temperature soldering in accordance with CECC 802 / Reflow guaranteed



MECHANICAL DATA

Case: JEDEC TO-263AB molded plastic body

Terminals: Lead solderable per MIL-STD-750, Method 2026

Polarity: As marked

Mounting Position: Any

Weight: 0.08 ounces, 2.24 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

	SYMBOLS	MBRB735	MBRB745	MBRB750	MBRB760	UNITS
Maximum repetitive peak reverse voltage	V _{RRM}	35	45	50	60	Volts
Maximum working peak reverse voltage	V _{RWM}	35	45	50	60	Volts
Maximum DC blocking voltage	V _{DC}	35	45	50	60	Volts
Maximum average forward rectified current (SEE FIG 1)	I _(AV)			7.5		Amps
Peak repetitive forward current (square wave, 20 KHz) at T _C =105°C	I _{FRM}			15.0		Amps
Peak forward surge current, 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}			150.0		Amps
Peak repetitive reverse surge current (NOTE 1)	I _{RRM}		1.0		0.5	Amps
Maximum instantaneous forward voltage at (NOTE 2)	I _F =7.5A, T _C =25°C I _F =7.5A, T _C =125°C I _F =15A, T _C =25°C I _F =15A, T _C =125°C	V _F	- 0.57 0.84 0.72	0.75 0.65 - -		Volts
Maximum instantaneous reverse current at rated DC blocking voltage (NOTE 1)	T _C =25°C T _C =125°C	I _R	0.1 15.0	0.5 50.0		mA
Voltage rate of change (rated V _R)	dV/dt		10,000		1,000	V/μs
Maximum thermal resistance, (NOTE 3)	R _{θJC}			3.0		°C/W
Operating junction temperature range	T _J			-65 to +150		°C
Storage temperature range	T _{STG}			-65 to +175		°C

NOTES:

(1) 2.0μs, pulse width, f=1.0 KHz

(2) Pulse test: 300μs pulse width, 1% duty cycle

(3) Thermal resistance from junction to case

勝特力材料 886-3-5753170

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RATINGS AND CHARACTERISTIC CURVES MBRB735 THRU MBRB760

FIG. 1 - FORWARD CURRENT DERATING CURVE

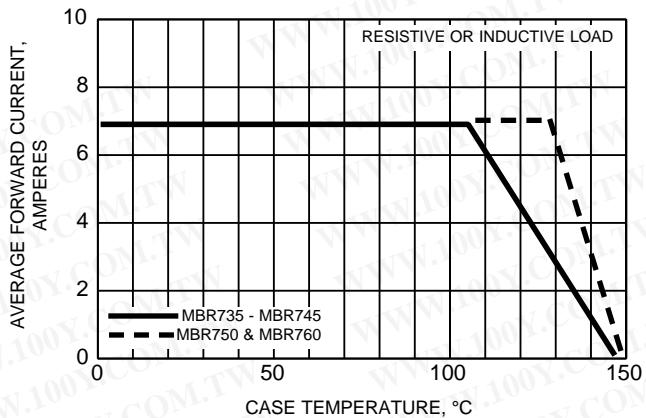


FIG. 2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

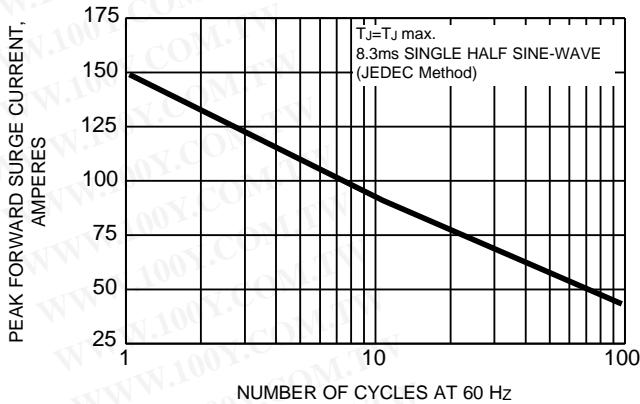


FIG. 3 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

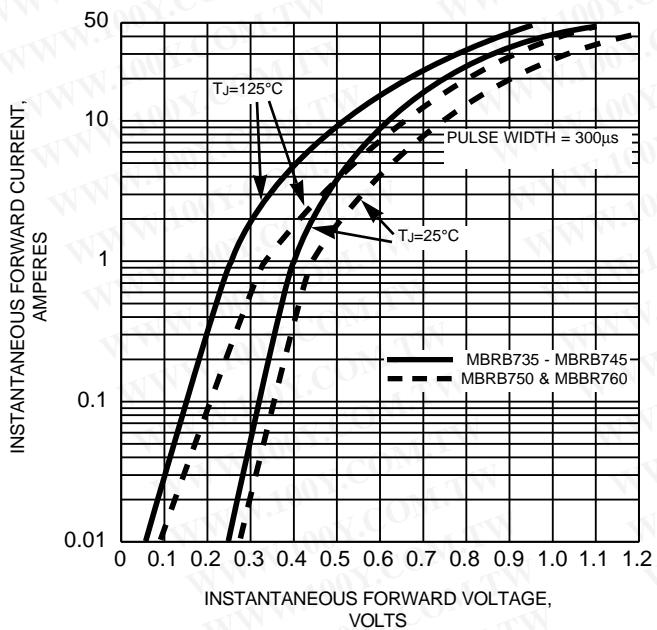


FIG. 4 - TYPICAL REVERSE CHARACTERISTICS

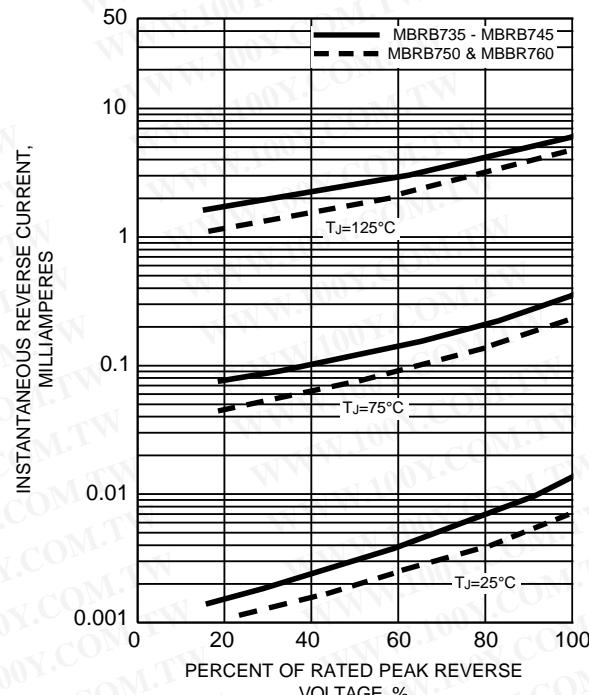


FIG. 5 - TYPICAL JUNCTION CAPACITANCE

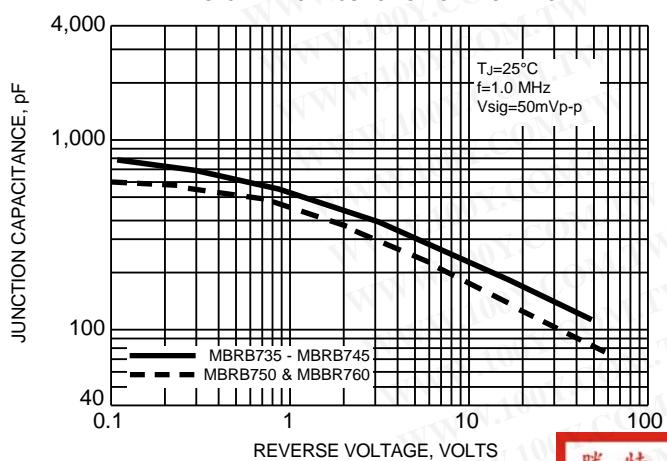
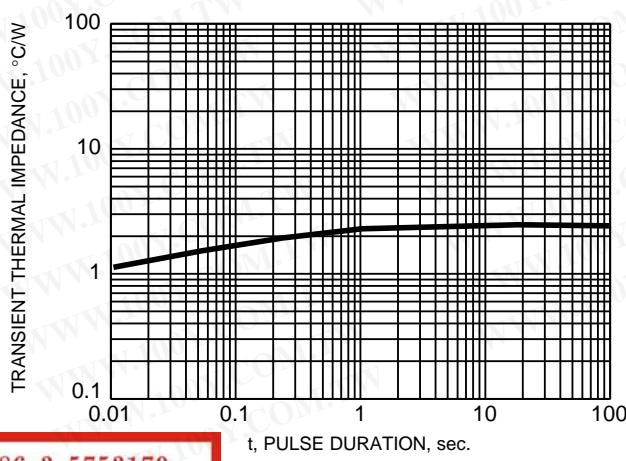


FIG. 6 - TYPICAL TRANSIENT THERMAL IMPEDANCE



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